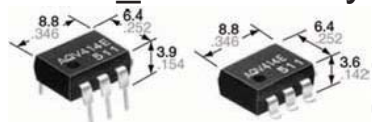


Relays & Solenoids

NAIS PCB Relays

Detailed product specifications are available on: us.100y.com.tw



FEATURES

1. 60V type couples high capacity (0.55A) with low on-resistance (1Ω).

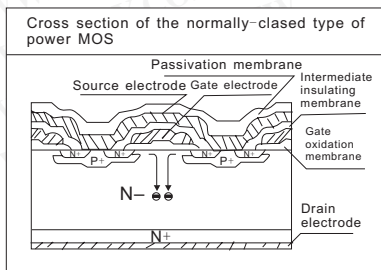
Item	GU-E (1 Form B type) type	
Part No.	AQV410EH	AQV412EH
Load voltage	350V	60V
Continuous load current	0.13A	0.55A
ON resistance (typ.)	18Ω	1Ω

2. This is the low-cost version PhotoMOS 1 Form B output type relay.

Compared to the previous GU PhotoMOS 1 Form B type relay, the attainment of an economical price that is approximately 22% lower will further broaden its market.

3. Normally closed type (2 Form B) is low on-resistance.

(All AQO4 PhotoMOS are Form B types. And also the Form A types have a low on-resistance.) This has been realized thanks to the built-in MOSFET processed by our proprietary method, DSD (Double-diffused and Selective Doping) method.



4. Controls low-level analog signals

PhotoMOS relays feature extremely low closed-circuit offset voltage to enable control of low-level analog signals without distortion.

5. High sensitivity, low ON resistance

Can control a maximum 0.13 A load current with a 5 mA input current. Low ON resistance of 18 Ω (AQV410EH). Stable operation because there are no metallic contact parts.

6. Low-level off-state leakage current

The SSR has an off-state leakage current of several milliamperes, whereas the PhotoMOS relay has typ. 100 pA even with the rated load voltage of 400 V (AQV414E).

7. Reinforced insulation 5,000 V type also available.

More than 0.4 mm internal insulation distance between inputs and outputs. Conforms to EN41003, EN60950 (reinforced insulation).

TYPICAL APPLICATIONS

- Security equipment
- Power supply
- Measuring equipment
- Telephone equipment
- Sensors



Part No.	Product No.	Manufacturer	Description	Contact Arrangement	Contact Rating	Coil Voltage	Recognized Safety	Type
47312	AQV410EH	NAIS	NAIS_GU-E PhotoMOS RELAY	1 Form B	350V / 130mA	350V	UL(E43149),C-UL,BSI	AQV410EH
47311	AQV412EH	NAIS	NAIS_GU-E PhotoMOS RELAY	1 Form B	60V / 550mA	60V	UL(E43149),C-UL	AQV412EH
47305	AQV414E	NAIS	NAIS_GU-E PhotoMOS RELAY	1 Form B	400V / 120mA	400V	UL(E43149),C-UL	AQV414E
47313	AQV414EH	NAIS	NAIS_GU-E PhotoMOS RELAY	1 Form B	400V / 120mA	400V	UL(E43149),C-UL,BSI,VDE	AQV414EH



FEATURES

1. Low on resistance for normally-closed type

This has been realized thanks to the built-in MOSFET processed by our proprietary method, DSD (Double-diffused and Selective Doping) method.

2. Controls low-level analog signals

PhotoMOS relays feature extremely low closed-circuit offset voltage to enable control of low-level analog signals without distortion.

3. High sensitivity, low ON resistance

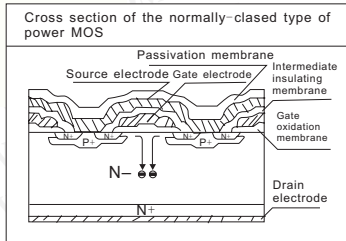
Can control a maximum 0.15 A load current with a 5 mA input current.

4. Low-level off state leakage current

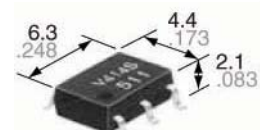
The SSR has an off state leakage current of several milliamperes, whereas the PhotoMOS relay has typ. 100 pA even with the rated load voltage of 400 V.

TYPICAL APPLICATIONS

- Telephone equipment (Dial pulse)
- Measuring equipment



Part No.	Product No.	Manufacturer	Description	Contact Arrangement	Contact Rating	Coil Voltage	Recognized Safety	Type
47247	AQV414	NAIS	NAIS_GU PhotoMOS Relay	1 Form B	400V/120mA	400V	UL(E43149),C-UL	AQV414



FEATURES

1. 1 channel (Form B) in super miniature design

The device comes in a super-miniature SO package measuring (W) 4.4 × (L) 6.3 × (H) 2.1 mm (W) .173 × (L) .248 × (H) .083 inch — approx. 25% of the volume and 50% of the footprint size of DIP type PhotoMOS Relays.

2. Low on resistance (Max. 50 Ω) at 400 V for normally-closed type

has been achieved thanks to the built-in MOSFET processed by our proprietary method, DSD (Double-Diffused and Selective Doping) method.

3. Tape and reel

The device comes standard in a tape and reel (1,000 pcs./reel) to facilitate automatic insertion machines.

4. Controls low-level analog signals

PhotoMOS relays feature extremely low closed-circuit offset voltage to enable control of low-level analog signals without distortion.

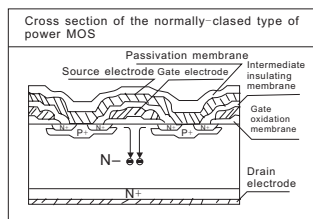
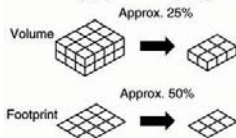
5. Low-level off state leakage current

In contrast to the SSR with an off state leakage current of several milliamperes, the PhotoMOS relay features a very small off state leakage current of typ. 100 pA even at the rated load voltage of 400 V.

6. Low thermal electromotive force (Approx. 1 μV)

TYPICAL APPLICATIONS

- Telephones
- Measuring instruments
- Computer
- Industrial robots
- High-speed inspection machines



Part No.	Product No.	Manufacturer	Description	Contact Arrangement	Contact Rating	Coil Voltage	Recognized Safety	Type
47245	AQV414S	NAIS	NAIS_GU PhotoMOS Relay	1-Channel (Form B)	400V / 100mA	400V	UL(E43149),C-UL	AQV414S



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